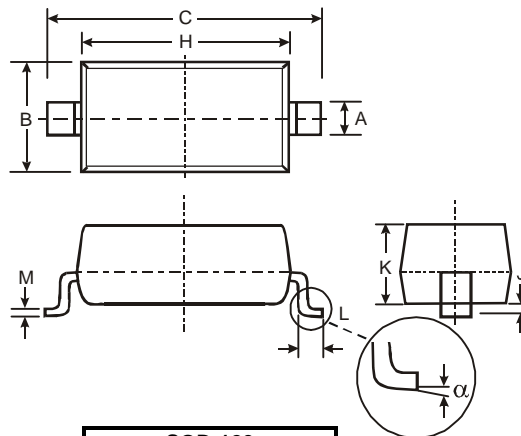


Features

- Silicon Epitaxial Planar Diode
- Fast switching diode, especially suited for applications requiring high voltage capability
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Mechanical Data

- **Case:** SOD123 plastic case
- **Weight:** approx. 9.3 mg
- **Packaging Codes/Options:**
GS18/10 k per 13" reel (8 mm tape), 10 k/box
GS08/3 k per 7" reel (8 mm tape), 15 k/box

SOD-123		
Dim	Min	Max
A	0.55 Typ	
B	1.40	1.70
C	3.55	3.85
H	2.55	2.85
J	0.00	0.10
K	1.00	1.35
L	0.25	0.40
M	0.10	0.15
α	0	8°
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit		
Continuous reverse voltage		V _R	240	V		
Peak repetitive reverse voltage		V _{RRM}	300	V		
Forward current (continuous)		I _F	225	mA		
Peak repetitive forward current		I _{FRM}	625	mA		
Non-repetitive peak forward current	t _p = 1 μs	I _{FSM}	4.0	A		
	t _p = 1 s	I _{FSM}	1.0	A		
Power dissipation		P _{tot}	350	mW		
Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	I _R = 100 μA	V _{BR}	300			V
Leakage current	V _R = 240 V	I _R			100	nA
	V _R = 240 V, T _j = 150 °C	I _R			100	μA
Forward voltage	I _F = 20 mA	V _F		0.83	0.87	V
	I _F = 100 mA	V _F			1.00	V
Diode capacitance	V _F = V _R = 0, f = 1 MHz	C _{tot}			5.0	pF
Reverse recovery time	I _F = I _R = 30 mA, I _{rr} = 3.0 mA, R _L = 100 Ω	t _{rr}			50	ns